

## High Sensitive InGaAs Photodiode

### Specifications

#### Absolute Maximum Ratings

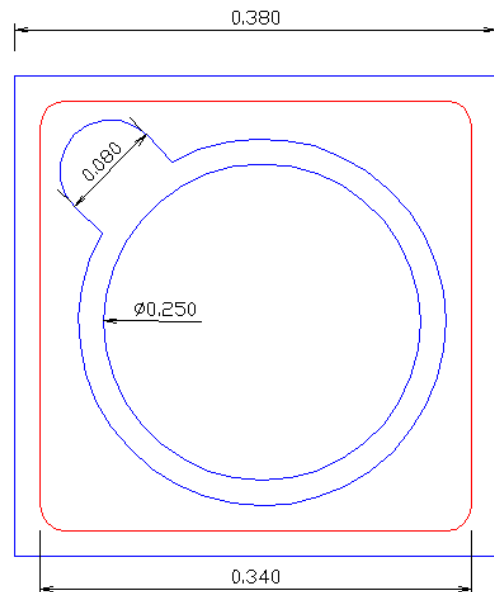
Parameter	Symbol	Value	Unit
Reverse voltage	$V_R$	20	V
Maximum optical power input	$P_{i\ max}$	10	mW
Forward current	$I_F$	10	mA
Operating temperature	$T_{opr}$	-40 to +85	°C
Storage temperature	$T_{stg}$	-40 to +85	°C

#### Electrical and Optical characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Active diameter	D	250			μm	
Bandwidth	BW		600		MHz	$P_i=-10\text{dBm}$ , small signal modulation, $V_R=5\text{V}$
Responsivity	R	0.8	0.9		A/W	$\lambda=1310\text{nm}$ , $V_R=5\text{V}$
		0.9	0.95			$\lambda=1550\text{nm}$ , $V_R=5\text{V}$
Dark current	$I_D$		0.1	1	nA	$V_R=5\text{V}$
Chip capacitance	$C_{chip}$		4.0	6.0	pF	$V_R=5\text{V}$ , $f=1\text{MHz}$
Total capacitance	$C_t$		4.0	6.0	pF	$V_R=5\text{V}$ , $f=1\text{MHz}$

### Dimensions

- Chip size: 380 x 380μm ( $\pm 25\mu\text{m}$ )
- Thickness:  $150 \pm 20\mu\text{m}$
- Active diameter:  $\phi 250\mu\text{m}$
- P-bond pad:  $\phi 80\mu\text{m}$



Unit: mm

Specifications are subject to change without notice.